

# DIODE MODULE

# DD(KD)100GB40/80



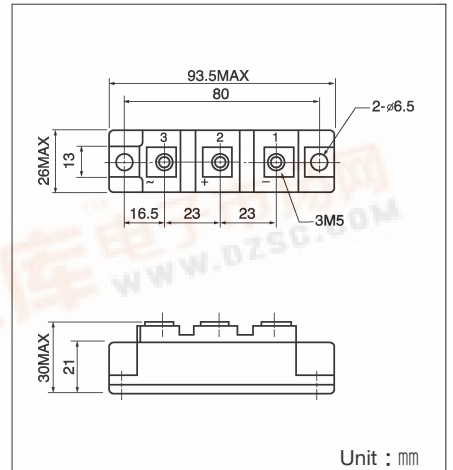
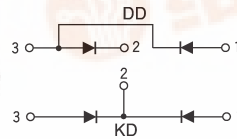
UL;E76102 (M)

Power Diode Module **DD100GB** series are designed for various rectifier circuits. **DD100GB** has two diode chips connected in series and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 800V is available for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

**(Applications)**

Various rectifiers, Battery chargers, DC motor drives



**Maximum Ratings**

(Tj=25°C)

Symbol	Item	Ratings		Unit
		DD100GB40	DD100GB80	
VRRM	Repetitive Peak Reverse Voltage	400	800	V
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	V

Symbol	Item	Conditions	Ratings	Unit	
IF (AV)	Average Forward Current	Single phase, half wave, 180° conduction, Tc : 115°C	100	A	
IF (RMS)	R.M.S. Forward Current	Single phase, half wave, 180° conduction, Tc : 115°C	155	A	
IFSM	Surge Forward Current	1/2 cycle, 50/60Hz, peak value, non-repetitive	1800/2000	A	
I²t	I²t	Value for one cycle of surge current	16500	A²S	
Tj	Junction Temperature		-40~+150	°C	
Tstg	Storage Temperature		-40~+125	°C	
Viso	Isolation Breakdown Voltage (R.M.S.)	A.C.1minute	2500	V	
	Mounting Torque	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	
	Mass			170	g

**Electrical Characteristics**

Symbol	Item	Conditions	Ratings	Unit
IRRM	Repetitive Peak Reverse Current, max.	at VDRM, single phase, half wave. Tj=150°C	30	mA
VFM	Forward Voltage Drop, max.	Foward current 320A, Tj=25°C, Inst. measurement	1.25	V
Rth (j-c)	Thermal Impedance, max.	Junction to case	0.30	°C/W



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